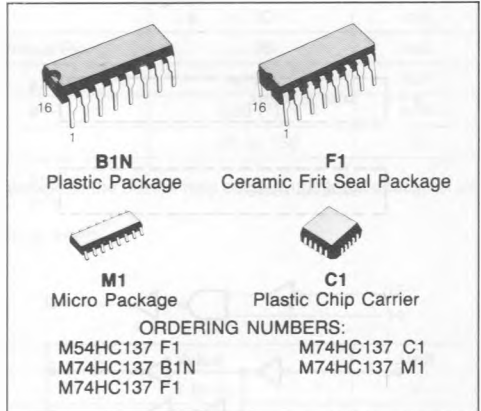


3 TO 8 LINE DECODER/LATCH (INVERTING)

- HIGH SPEED
 $t_{PD} = 14 \text{ ns (TYP.) at } V_{CC} = 5V$
- LOW POWER DISSIPATION
 $I_{CC} = 4 \mu\text{A (MAX.) at } T_A = 25^\circ\text{C}$
- HIGH NOISE IMMUNITY
 $V_{NIH} = V_{NIL} = 28\% V_{CC} \text{ (MIN.)}$
- OUTPUT DRIVE CAPABILITY
 10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
 $|I_{OH}| = |I_{OL}| = 4 \text{ mA (MIN.)}$
- BALANCED PROPAGATION DELAYS
 $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE
 $V_{CC} \text{ (OPR)} = 2V \text{ to } 6V$
- PIN AND FUNCTION COMPATIBLE
 WITH 54/74LS137



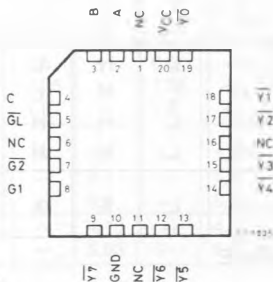
DESCRIPTION

The M54/74HC137 is a high speed CMOS 3 TO 8 LINE DECODER/LATCH (INVERTING) fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption.

This device is a 3 to 8 line decoder with latches on the three address inputs. When \overline{GL} goes from low to high, the address present at the select inputs (A, B and C) is stored in the latches. As long as \overline{GL} remains high no address changes will be recognized. Output enable pins G1 and G2, control the state of the outputs independently of the select or latch-enable inputs. All the outputs are high unless G1 and G2 are low. The HC137 is ideally suited for the implementation of glitch-free decoders in stored-address applications in bus oriented systems.

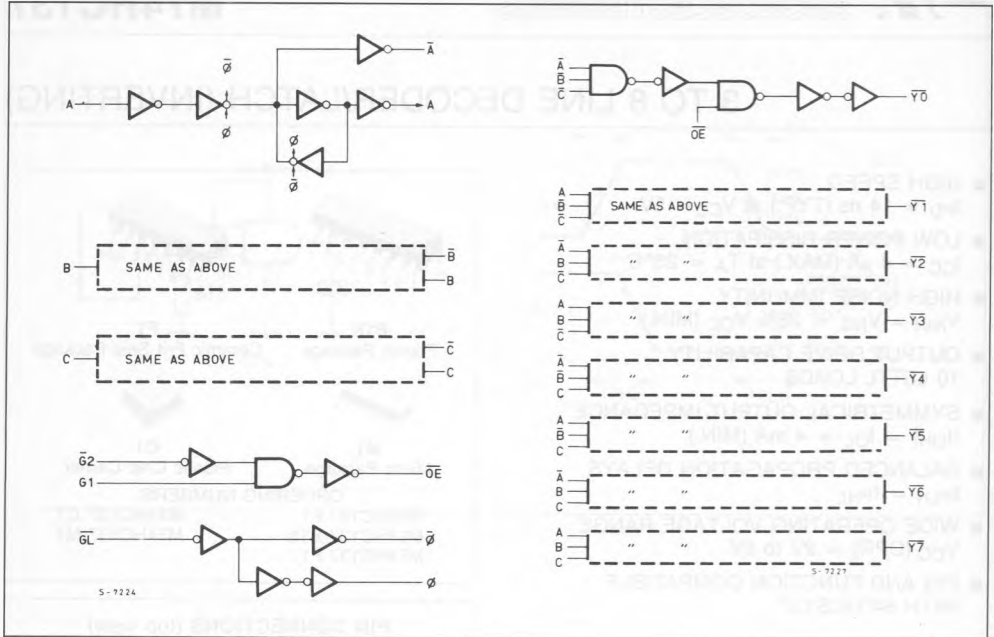
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTIONS (top view)



NC =
 No Internal
 Connection

LOGIC DIAGRAM



TRUTH TABLE

INPUTS						OUTPUTS							
ENABLE			SELECT			$Y0$	$Y1$	$Y2$	$Y3$	$Y4$	$Y5$	$Y6$	$Y7$
$\bar{G}L$	$G1$	$\bar{G}2$	C	B	A								
X	X	H	X	X	X	H	H	H	H	H	H	H	H
X	L	X	X	X	X	H	H	H	H	H	H	H	H
L	H	L	L	L	L	L	H	H	H	H	H	H	H
L	H	L	L	L	H	H	L	H	H	H	H	H	H
L	H	L	L	H	L	H	H	L	H	H	H	H	H
L	H	L	L	H	H	H	H	H	L	H	H	H	H
L	H	L	H	L	L	H	H	H	H	H	L	H	H
L	H	L	H	L	H	H	H	H	H	H	H	L	H
L	H	L	H	H	L	H	H	H	H	H	H	L	H
L	H	L	H	H	H	H	H	H	H	H	H	H	L
H	H	L	X	X	X	Outputs corresponding to stored address L: all others H							

X: DON'T CARE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	- 0.5 to 7	V
V _I	DC Input Voltage	- 0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	- 0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Source Sink Current Per Output Pin	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	- 65 to 150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: ≡ 65°C derate to 300 mW by 10 mW/°C: 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V _{CC}	Supply Voltage	2 to 6	V	
V _I	Input Voltage	0 to V _{CC}	V	
V _O	Output Voltage	0 to V _{CC}	V	
T _A	Operating Temperature	74HC Series 54HC Series	- 40 to 85 - 55 to 125	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} { 2 V 4.5V 6 V	0 to 1000 0 to 500 0 to 400	ns

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	V _{CC}	Test Condition	T _A = 25°C 54HC and 74HC			- 40 to 85°C 74HC		- 55 to 125°C 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	2.0		1.5	—	—	1.5	—	1.5	—	V
		4.5		3.15	—	—	3.15	—	3.15	—	
		6.0		4.2	—	—	4.2	—	4.2	—	
V _{IL}	Low Level Input Voltage	2.0		—	—	0.5	—	0.5	—	0.5	V
		4.5		—	—	1.35	—	1.35	—	1.35	
		6.0		—	—	1.8	—	1.8	—	1.8	
V _{OH}	High Level Output Voltage	2.0	V _I	1.9	2.0	—	1.9	—	1.9	—	V
		4.5	V _{IH} or V _{IL}	4.4	4.5	—	4.4	—	4.4	—	
		6.0		5.9	6.0	—	5.9	—	5.9	—	
		4.5	- 20 μA	4.18	4.31	—	4.13	—	4.10	—	
		6.0		- 4.0 mA	5.68	5.8	—	5.63	—	5.60	
	- 5.2 mA										

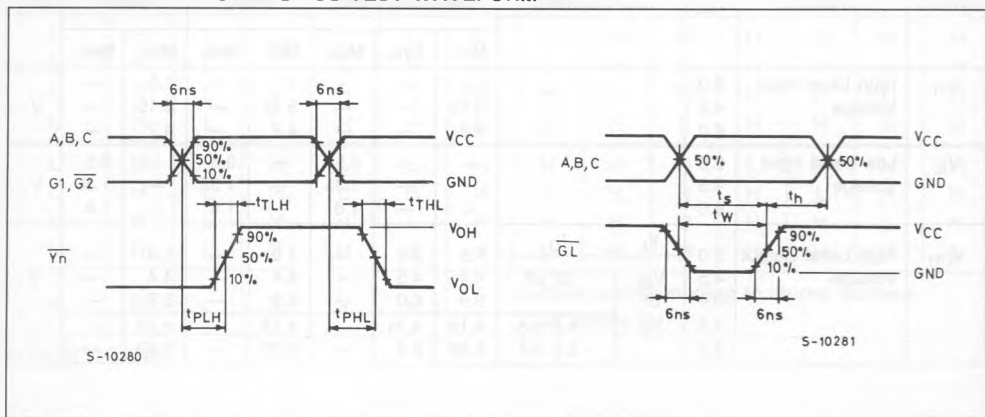
DC ELECTRICAL CHARACTERISTICS (Continued)

Symbol	Parameter	V _{CC}	Test Condition	T _A = 25°C 54HC and 74HC			- 40 to 85°C 74HC		- 55 to 125°C 54HC		Unit	
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.		
				V _{OL}	Low Level Output Voltage	2.0 4.5 6.0 4.5 6.0	V _I	I _O	—	0.0		0.1
V _{IH} or V _{IL}	20 μA	—	0.0				0.1	—	0.1	—	0.1	
	4.0 mA	—	0.17				0.26	—	0.33	—	0.40	
	5.2 mA	—	0.18				0.26	—	0.33	—	0.40	
I _I	Input Leakage Current	6.0	V _I = V _{CC} or GND	—	—	±0.1	—	±1.0	—	±1.0	μA	
I _{CC}	Quiescent Supply Current	6.0	V _I = V _{CC} or GND	—	—	4	—	40	—	80	μA	

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5V, T_A = 25°C, C_L = 15pF, Input t_r = t_f = 6ns)

Symbol	Parameter	54HC and 74HC			Unit
		Min.	Typ.	Max.	
t _{TLH} t _{THL}	Output Transition Time		4	8	ns
t _{PLH} t _{PHL}	Propagation Delay Time (G1 - Y _n)		14	23	ns
t _{PLH} t _{PHL}	Propagation Delay Time (G2 - Y _n)		17	26	ns
t _{PLH} t _{PHL}	Propagation Delay Time (GL - Y _n)		24	38	ns
t _{PLH} t _{PHL}	Propagation Delay Time (A,B,C - Y _n)		21	34	ns

SWITCHING CHARACTERISTICS TEST WAVEFORM



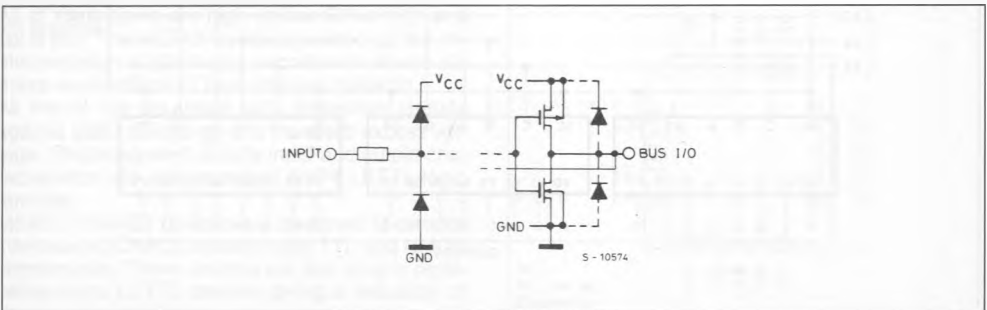
AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

Symbol	Parameter	V_{CC}	Test Condition	$T_A = 25^\circ\text{C}$ 54HC and 74HC			$-40\text{ to }85^\circ\text{C}$ 74HC		$-55\text{ to }125^\circ\text{C}$ 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} t_{THL}	Output Transition Time	2.0		—	30	75	—	95		110	ns
		4.5		—	8	15	—	19		22	
		6.0		—	7	13	—	16		19	
t_{PLH} t_{PHL}	Propagation Delay Time ($G1-\bar{Y}_n$)	2.0		—	72	145	—	180		220	ns
		4.5		—	18	29	—	36		44	
		6.0		—	15	25	—	31		38	
t_{PLH} t_{PHL}	Propagation Delay Time ($G2-\bar{Y}_n$)	2.0		—	80	155	—	195		235	ns
		4.5		—	20	31	—	39		47	
		6.0		—	17	26	—	33		40	
t_{PLH} t_{PHL}	Propagation Delay Time ($\bar{G}L - \bar{Y}_n$)	2.0		—	112	220	—	275		330	ns
		4.5		—	28	44	—	55		66	
		6.0		—	24	37	—	47		56	
t_{PLH} t_{PHL}	Propagation Delay Time (A,B,C - \bar{Y}_n)	2.0		—	100	195	—	245		295	ns
		4.5		—	25	39	—	49		59	
		6.0		—	21	33	—	42		50	
$t_{W(L)}$	Minimum Pulse Width ($\bar{G}L$)	2.0		—	30	75	—	95		110	ns
		4.5		—	8	15	—	19		22	
		6.0		—	7	13	—	16		19	
t_s	Minimum Set-up Time (A,B,C $\bar{G}L$)	2.0		—	10	50	—	65		75	ns
		4.5		—	2	10	—	13		15	
		6.0		—	2	9	—	11		13	
t_h	Minimum Hold Time (A,B,C $\bar{G}L$)	2.0		—	5	25	—	30	—	40	ns
		4.5		—	0	5	—	6	—	8	
		6.0		—	0	5	—	6	—	7	
C_{IN}	Input Capacitance			—	5	10	—	10		10	pF
$C_{PD} (*)$	Power Dissipation Capacitance			—	65	—	—	—			pF

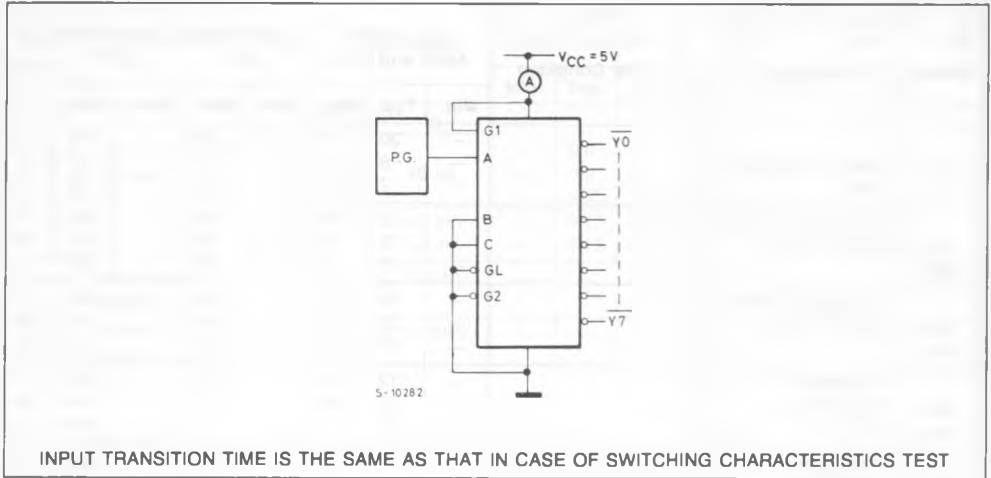
Note (*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit)

Average operating current can be obtained by the following: $I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

INPUT AND OUTPUT EQUIVALENT CIRCUIT



TEST CIRCUIT I_{CC} (Opr.)



TYPICAL APPLICATION

